



# PSMN015-60BS

N-channel 60 V 14.8 mΩ standard level MOSFET in D2PAK

Rev. 2 — 1 March 2012

Product data sheet

## 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

### 1.3 Applications

- DC-to-DC converters
- Motor control
- Load switching
- Server power supplies

### 1.4 Quick reference data

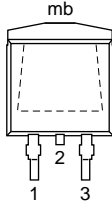
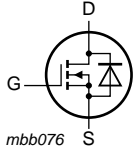
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$	-	-	60	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; see <a href="#">Figure 1</a>	-	-	50	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	-	86	W
$T_j$	junction temperature		-55	-	175	°C
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$ ; $I_D = 15\text{ A}$ ; $T_j = 100\text{ °C}$ ; see <a href="#">Figure 12</a>	-	-	23.7	mΩ
		$V_{GS} = 10\text{ V}$ ; $I_D = 15\text{ A}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 13</a>	-	12.6	14.8	mΩ
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10\text{ V}$ ; $I_D = 25\text{ A}$ ; $V_{DS} = 30\text{ V}$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	4.7	-	nC
$Q_{G(tot)}$	total gate charge		-	20.9	-	nC
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ °C}$ ; $I_D = 50\text{ A}$ ; $V_{sup} \leq 60\text{ V}$ ; $R_{GS} = 50\text{ Ω}$ ; unclamped	-	-	44	mJ



## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain <sup>[1]</sup>		
3	S	source		
mb	D	mounting base; connected to drain		

**SOT404 (D2PAK)**

[1] It is not possible to make connection to pin 2

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN015-60BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$	-	60	V
$V_{DGR}$	drain-gate voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$ ; $R_{GS} = 20\text{ k}\Omega$	-	60	V
$V_{GS}$	gate-source voltage		-20	20	V
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; see <a href="#">Figure 1</a>	-	36	A
		$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 1</a>	-	50	A
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 3</a>	-	201	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	86	W
$T_{stg}$	storage temperature		-55	175	°C
$T_j$	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
<b>Source-drain diode</b>					
$I_S$	source current	$T_{mb} = 25\text{ °C}$	-	50	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$	-	201	A
<b>Avalanche ruggedness</b>					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ °C}$ ; $I_D = 50\text{ A}$ ; $V_{sup} \leq 60\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; unclamped	-	44	mJ

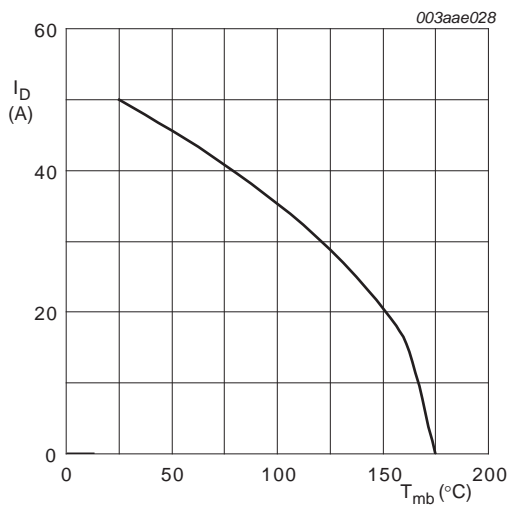
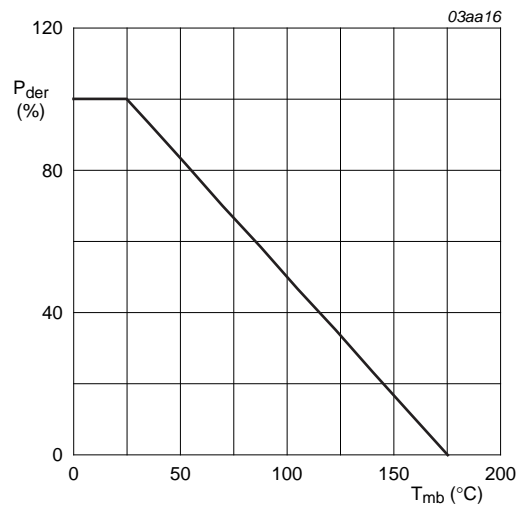


Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature

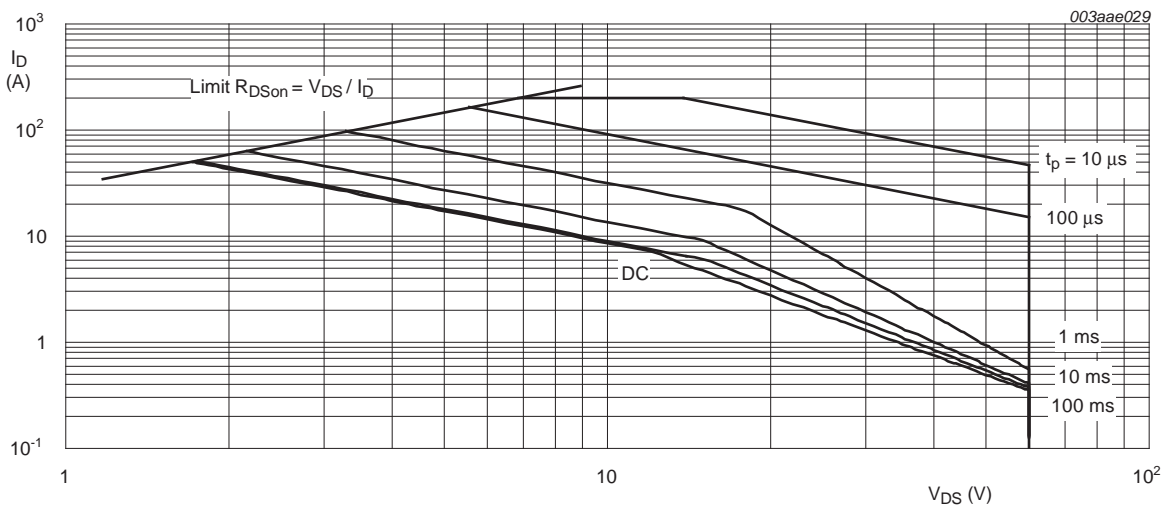
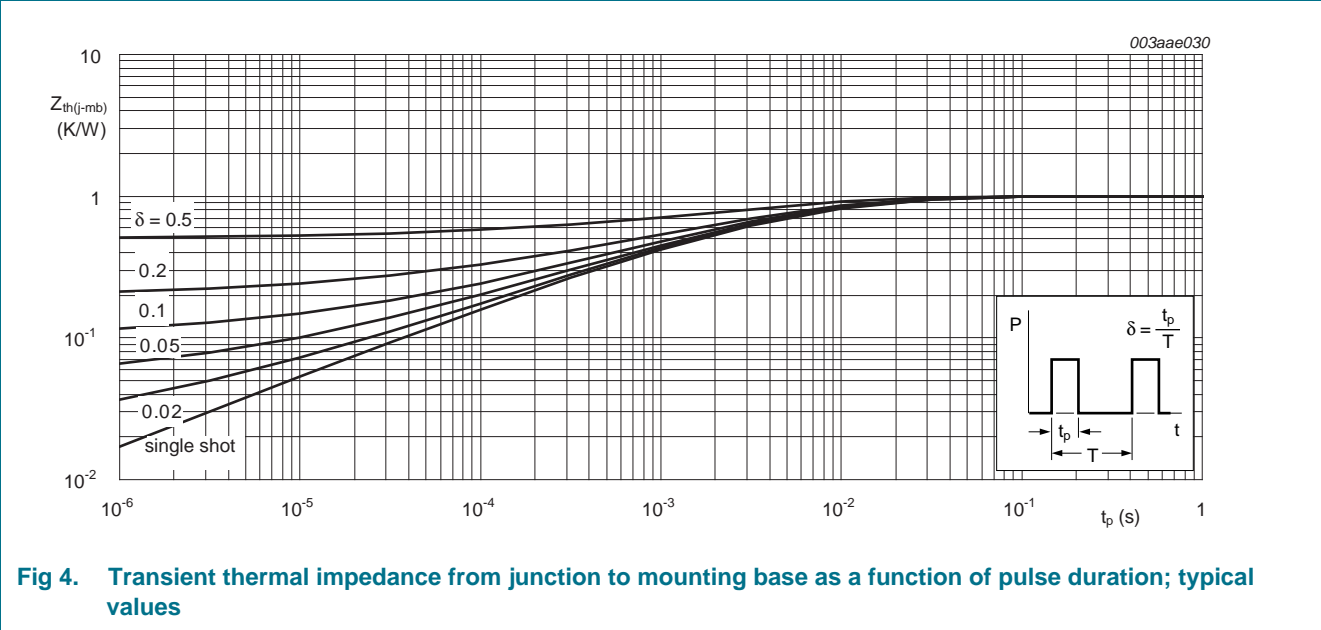


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 4</a>	-	1	1.74	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	60	-	K/W



## 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\ \mu A$ ; $V_{GS} = 0\ V$ ; $T_j = -55\ ^\circ C$	54	-	-	V
		$I_D = 250\ \mu A$ ; $V_{GS} = 0\ V$ ; $T_j = 25\ ^\circ C$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\ mA$ ; $V_{DS} = V_{GS}$ ; $T_j = 25\ ^\circ C$ ; see <a href="#">Figure 10</a> ; see <a href="#">Figure 11</a>	2	3	4	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 1\ mA$ ; $V_{DS} = V_{GS}$ ; $T_j = -55\ ^\circ C$ ; see <a href="#">Figure 11</a>	-	-	4.8	V
		$I_D = 1\ mA$ ; $V_{DS} = V_{GS}$ ; $T_j = 175\ ^\circ C$ ; see <a href="#">Figure 11</a>	1	-	-	V
$I_{DSS}$	drain leakage current	$V_{DS} = 60\ V$ ; $V_{GS} = 0\ V$ ; $T_j = 25\ ^\circ C$	-	0.03	2	$\mu A$
		$V_{DS} = 60\ V$ ; $V_{GS} = 0\ V$ ; $T_j = 125\ ^\circ C$	-	-	30	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 20\ V$ ; $V_{DS} = 0\ V$ ; $T_j = 25\ ^\circ C$	-	10	100	nA
		$V_{GS} = -20\ V$ ; $V_{DS} = 0\ V$ ; $T_j = 25\ ^\circ C$	-	10	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10\ V$ ; $I_D = 15\ A$ ; $T_j = 175\ ^\circ C$ ; see <a href="#">Figure 12</a>	-	28.9	34	mΩ
		$V_{GS} = 10\ V$ ; $I_D = 15\ A$ ; $T_j = 100\ ^\circ C$ ; see <a href="#">Figure 12</a>	-	-	23.7	mΩ
		$V_{GS} = 10\ V$ ; $I_D = 15\ A$ ; $T_j = 25\ ^\circ C$ ; see <a href="#">Figure 13</a>	-	12.6	14.8	mΩ
$R_G$	gate resistance	$f = 1\ MHz$	-	1.3	-	Ω
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 25\ A$ ; $V_{DS} = 30\ V$ ; $V_{GS} = 10\ V$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	20.9	-	nC
		$I_D = 0\ A$ ; $V_{DS} = 0\ V$ ; $V_{GS} = 10\ V$	-	17	-	nC
$Q_{GS}$	gate-source charge	$I_D = 25\ A$ ; $V_{DS} = 30\ V$ ; $V_{GS} = 10\ V$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	6.2	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge	$I_D = 25\ A$ ; $V_{DS} = 30\ V$ ; $V_{GS} = 10\ V$ ; see <a href="#">Figure 14</a>	-	3.7	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	2.4	-	nC
$Q_{GD}$	gate-drain charge	$I_D = 25\ A$ ; $V_{DS} = 30\ V$ ; $V_{GS} = 10\ V$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	4.7	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$V_{DS} = 30\ V$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	4.8	-	V
$C_{iss}$	input capacitance	$V_{DS} = 30\ V$ ; $V_{GS} = 0\ V$ ; $f = 1\ MHz$ ;	-	1220	-	pF
$C_{oss}$	output capacitance	$T_j = 25\ ^\circ C$ ; see <a href="#">Figure 16</a>	-	169	-	pF
$C_{rss}$	reverse transfer capacitance		-	95	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30\ V$ ; $R_L = 1.2\ \Omega$ ; $V_{GS} = 10\ V$ ;	-	12	-	ns
$t_r$	rise time	$R_{G(ext)} = 4.7\ \Omega$	-	13	-	ns
$t_{d(off)}$	turn-off delay time		-	27	-	ns
$t_f$	fall time		-	7	-	ns

Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode						
$V_{SD}$	source-drain voltage	$I_S = 15\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 25\text{ °C}$	-	0.8	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 25\text{ A}$ ; $di_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 30\text{ V}$	-	31	-	ns
$Q_r$	recovered charge		-	28.5	-	nC

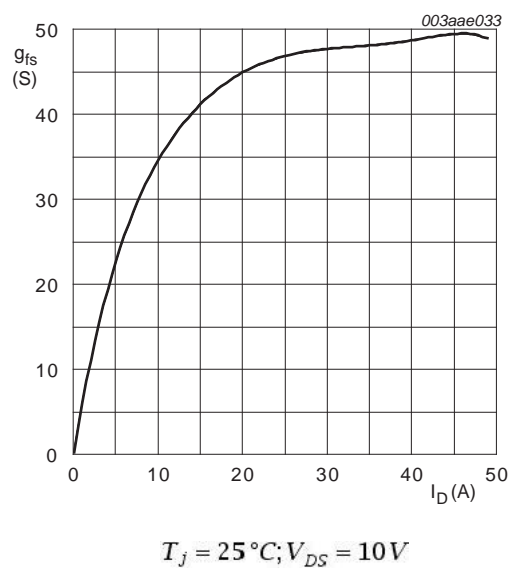


Fig 5. Forward transconductance as a function of drain current; typical values

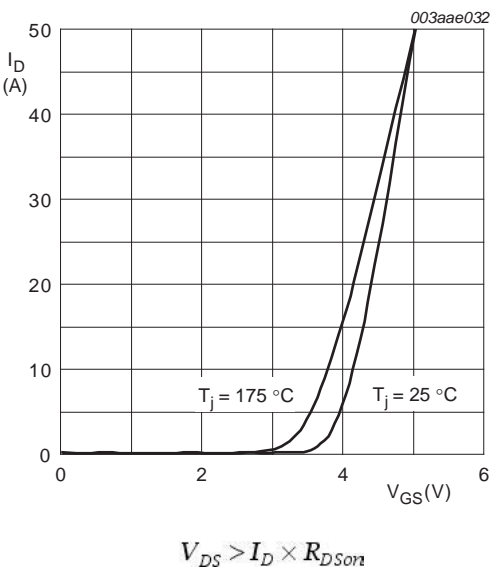


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

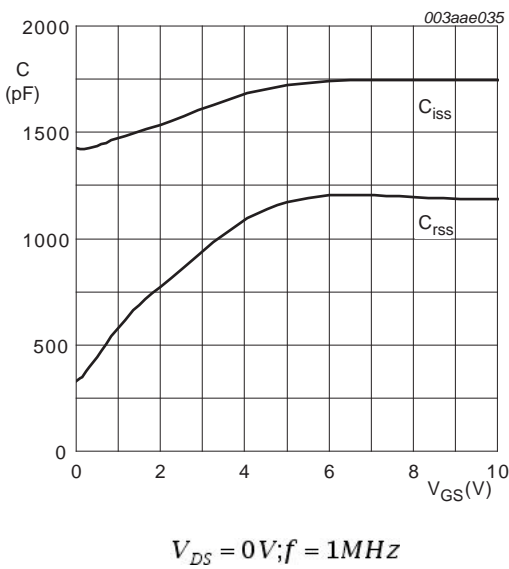


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

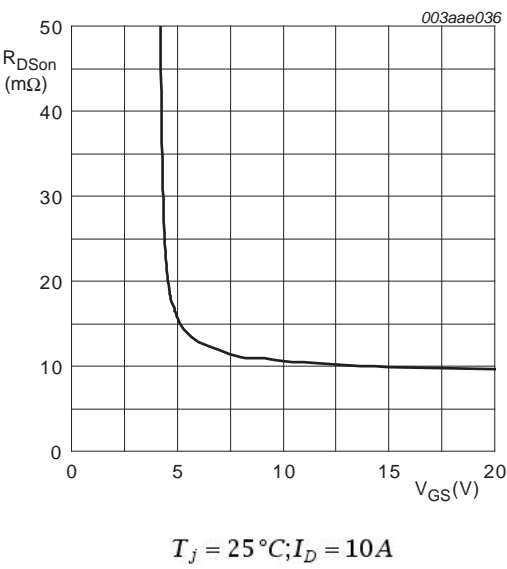


Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

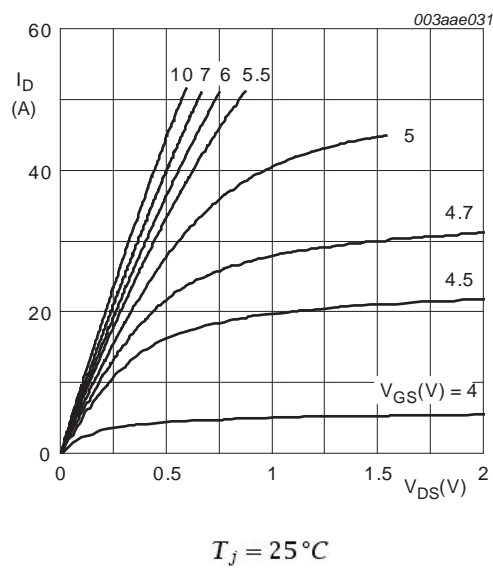


Fig 9. Output characteristics: drain current as a function of drain-source voltage; typical values

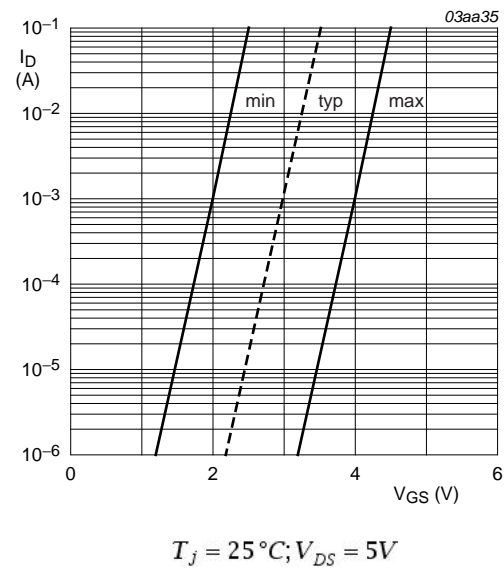


Fig 10. Sub-threshold drain current as a function of gate-source voltage

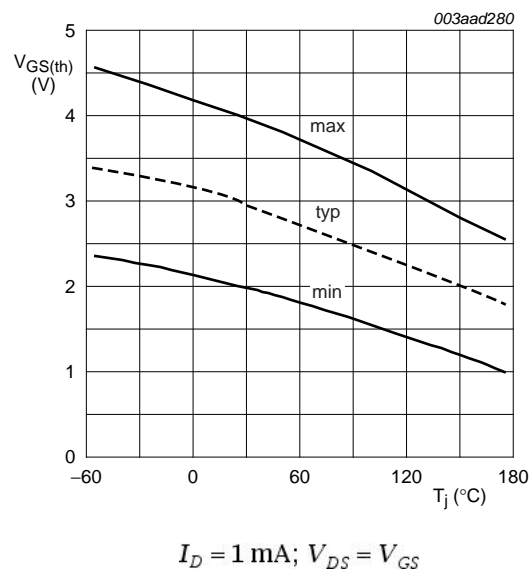


Fig 11. Gate-source threshold voltage as a function of junction temperature

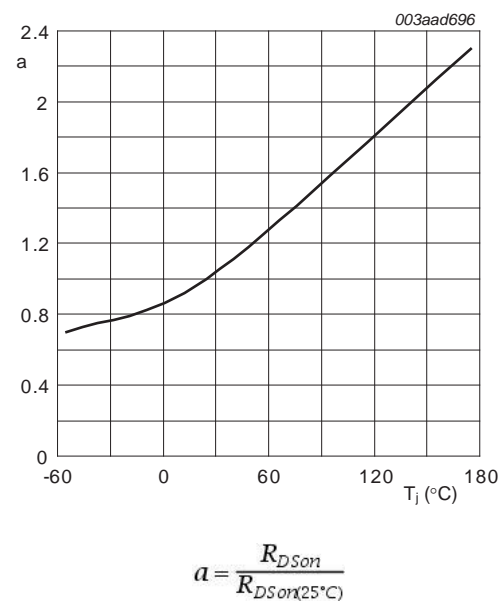


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature.

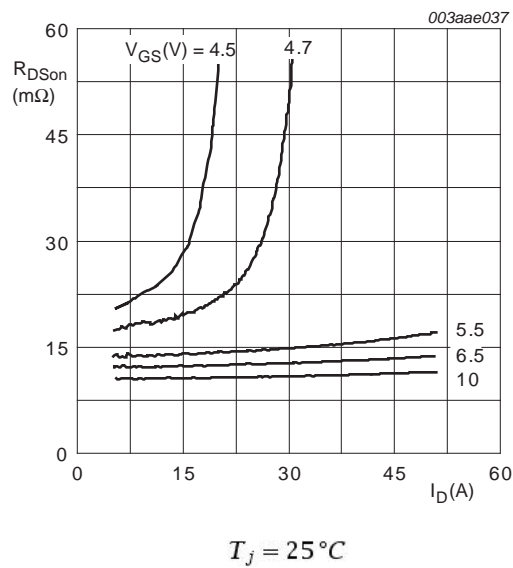


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

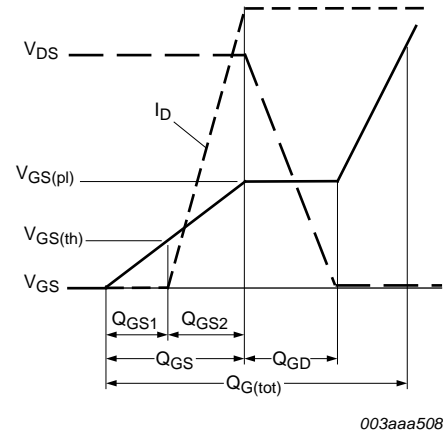


Fig 14. Gate charge waveform definitions

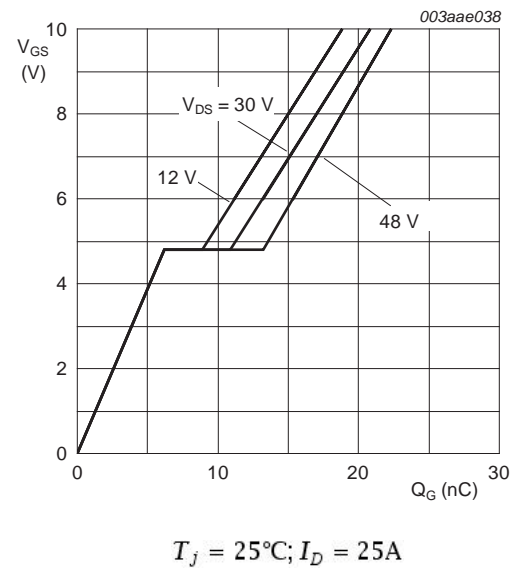


Fig 15. Gate-source voltage as a function of gate charge; typical values

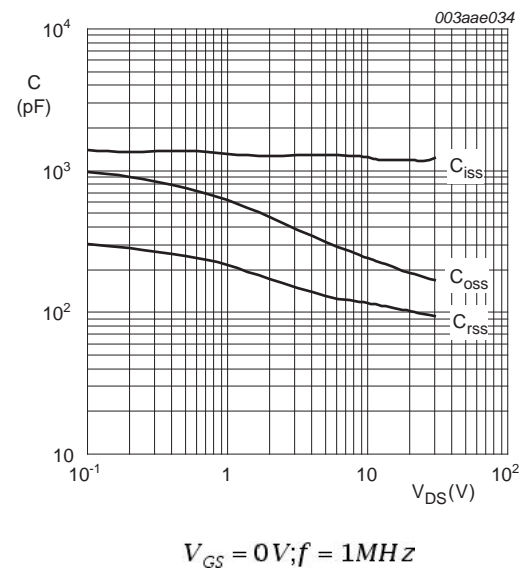


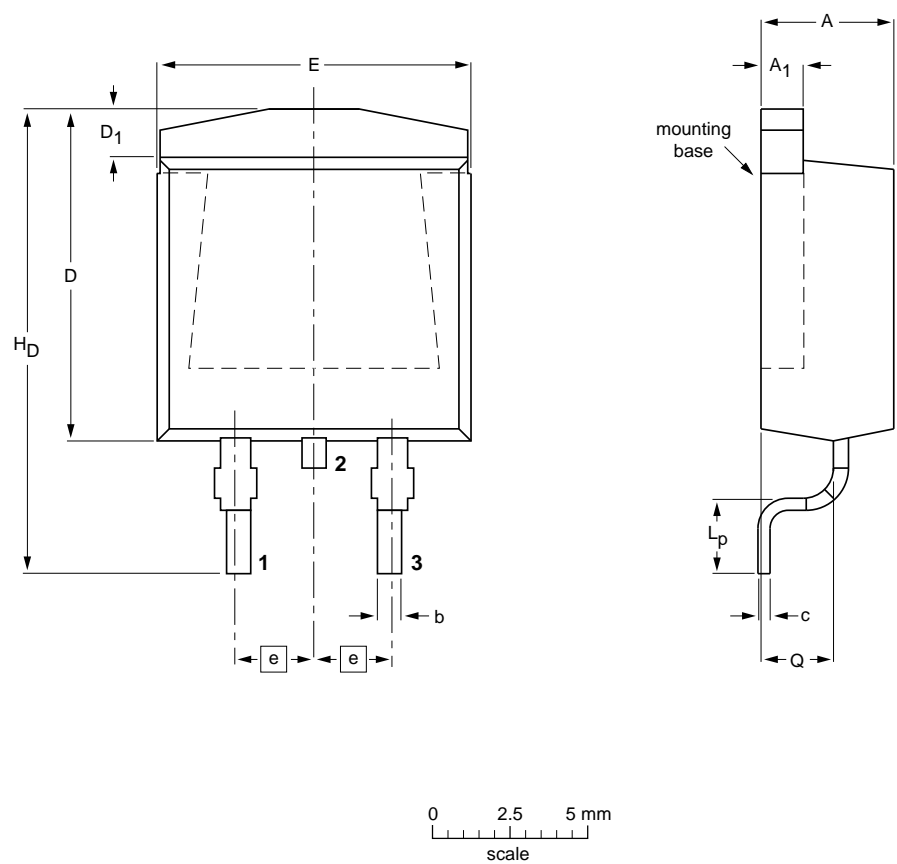
Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



7. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)

SOT404



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b	c	D <sub>max.</sub>	D <sub>1</sub>	E	e	L <sub>p</sub>	H <sub>D</sub>	Q
mm	4.50 4.10	1.40 1.27	0.85 0.60	0.64 0.46	11	1.60 1.20	10.30 9.70	2.54	2.90 2.10	15.80 14.80	2.60 2.20

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT404						05-02-11 06-03-16

Fig 17. Package outline SOT404 (D2PAK)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN015-60BS v.2	20120301	Product data sheet	-	PSMN015-60BS v.1
Modifications:	<ul style="list-style-type: none"><li>• Status changed from objective to product.</li><li>• Various changes to content.</li></ul>			
PSMN015-60BS v.1	20111021	Objective data sheet	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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For sales office addresses, please send an email to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

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